

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	4	"4,779,036"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 15:48
S2	2	"20020066904"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 15:49
S3	3	"6,091,087"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 15:50
S4	8	"3,824,444"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 15:51
S5	21	"3,344,310"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 15:51
S6	11	"4,630,092"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 15:52
S7	496	(gate base) with accumulation with pulse	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 09:34

S8	77	(scr transistor) same (gate base) with accumulation with pulse	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 09:35
S9	36	("20020066904" "3344310" "3663950" "3824444" "4296296" "4389691" "4459531" "4630092" "4649414" "4713723" "4760432" "4779036" "4982259" "5546038" "6091087").FN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 13:39
S10	10	("4713723").URFN.	USPAT	OR	OFF	2008/07/27 14:03
S11	23263	gate with accumulat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 14:25
S12	97	gate with accumulat\$3 with (high medium) with frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 14:26
S13	11	(transistor scr triac) with gate with accumulat\$3 with (high medium) with frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 14:30
S14	2688	(mos mosfet field adj effect) with gate near capacitance	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:11
S15	9	(mos mosfet field adj effect) with gate near capacitance with (recification rectify\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:13

S16	0	(scr triac four adj layer) with gate near capacitance with (recification rectify\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:23
S17	57	(mos mosfet field adj effect) with gate near capacitance with high near frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:23
S18	7	(mos mosfet field adj effect) with gate near capacitance with high near frequency same accumulats\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:24
S19	86	(mos mosfet field adj effect) with gate near capacitance same accumulats\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:26
S20	46	(mos mosfet field adj effect) with gate near capacitance with accumulats\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:26
S21	0	(mos mosfet field adj effect) with gate near capacitance with accumulats\$3 with subthreshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:27
S22	2	(mos mosfet field adj effect) with gate near capacitance with subthreshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:27
S23	0	(mos mosfet field adj effect) with gate near capacitance with sub adj hreshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:28

S24	5	(mos mosfet field adj effect) with gate near capacitance with sub adj threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:28
S25	0	(scr triac fou adj layer) with sub adj threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:32
S26	0	(scr triac four adj layer) with (sub adj threshold or su-threshold or subthreshold)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:32
S27	0	(scr triac four adj layer) with (sub adj threshold or sub-threshold or subthreshold)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:33
S28	1304	(mos mosfet field adj effect) with sub adj threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:33
S29	28	(mos mosfet field adj effect) with sub adj threshold with input near signal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:33
S30	6	(mos mosfet field adj effect) with sub adj threshold with input near signal and high near frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:38
S31	1	transistor with sub adj threshold with input near signal and high near frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:39

S32	0	transistor with "not" adj sufficient with input near signal and high near frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:44
S33	0	transistor same "not" adj sufficient with input near signal and high near frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:44
S34	0	transistor and "not" adj sufficient with input near signal and high near frequency	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:44
S35	0	transistor and high near frequency with "not" near sufficient	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:45
S36	8	transistor and high near frequency with under near threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:46
S37	9	transistor and high near frequency same under near threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:50
S38	232	transistor and high near frequency same below near threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:51
S39	57	transistor and high near frequency with below near threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:51

S40	1	transistor and high near frequency with below near threshold same capacitance	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 15:51
S41	8	transistor same capacitance and high near frequency with below near threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 16:13
S42	84	(scr thyristor) with trigger\$3 with (sub or below or under) with threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 17:40
S43	4	"4779036"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:03
S44	5	10/727,189	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:16
S45	5	("3959714" "4384213" "4434358" "4493984" "4589059").FN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/27 18:26
S46	2	("4779036").URPN.	USPAT	OR	OFF	2008/07/27 18:29
S47	2	"20020066904"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:31
S48	8	"3824444"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:33

S49	158	high near frequency with trigger\$3 with (scr triac thyristor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:40
S50	0	high near frequency with trigger\$3 with (scr triac thyristor) with non near rectif\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:41
S51	0	high near frequency with trigger\$3 with (scr triac thyristor) with (non no) near3 rectif\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:42
S52	1	high near frequency with trigger\$3 with (scr triac thyristor) same (below under sub) near threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:43
S53	1	high near frequency with trigger\$3 with (scr triac thyristor) same (below under sub) near3 threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:53
S54	0	high near frequency same trigger\$3 with (triac thyristor) same (below under sub) near3 threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:54
S55	4	high near frequency same trigger\$3 with (scr triac thyristor) same (below under sub) near3 threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 18:54
S56	21	"3,344,310"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 19:02

S57	2	(thyristor scr triac) with gate with high near frequency with insufficient	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 19:19
S58	2	(thyristor scr triac) same gate with high near frequency with insufficient	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 19:21
S59	4	(thyristor scr triac) same gate with high near frequency same insufficient	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 19:21
S60	0	(thyristor scr triac) same gate with high near frequency same under near threshold	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 20:55
S61	0	(thyristor scr triac) same gate with high near frequency same under near3 threshold	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 20:56
S62	0	(thyristor scr triac) same gate with high near frequency and under near3 threshold	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 20:57
S63	2	(thyristor scr triac) same gate with under near3 threshold	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 20:57
S64	0	(thyristor scr triac) same half near period with under near3 threshold	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 21:00

S65	0	(thyristor scr triac) same single near period with under near3 threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 21:01
S66	0	(thyristor scr triac) same single near pulse with under near3 threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/27 21:02
S67	4	high near frequency with trigger\$3 with (scr triac thyristor) same (below under sub) with threshold	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 10:08
S68	16	"3,588,525"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 10:13
S69	10	"4,575,642"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 10:14
S70	2	"7,221,066"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 10:15
S71	0	("7221066").URPN.	USPAT	OR	OFF	2008/07/28 10:16
S72	8	("3409805" "4622627" "4713723" "5654621" "5684445" "5929598" "5949155").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/28 10:17
S73	10	("4713723").URPN.	USPAT	OR	OFF	2008/07/28 10:20

S74	22	("3900770" "3953816" "3958075" "4021728" "4156148" "4196411" "4215235" "4218724" "4250481" "4257091" "4266140" "4394530" "4425511" "4449165" "4449292" "4488202" "4498120" "4546410" "4546411" "4554613" "4574162" "4577387").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/28 10:23
S75	9	"4,459,531"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:14
S76	16	"5546038"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:23
S77	17	"4,659,941"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:35
S78	14	"4,731,549"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:38
S79	27	"4,970,623"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:44
S80	43	radio near frequency with (scr triac thyristor) with gat\$3	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:46

S81	284	high near frequency with (scr triac thyristor) with gat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:55
S82	160	high near frequency with (scr triac thyristor) near3 (gate gating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:57
S83	118	high near frequency with (scr triac thyristor) near2 (gate gating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:57
S84	76	high near frequency with (scr triac thyristor) near (gate gating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:58
S85	29	high near frequency with signal with (scr triac thyristor) near (gate gating)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/28 11:58
S86	4	("3324355" "3582684" "3745379").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/28 12:11
S87	2	("3955104").URPN.	USPAT	OR	OFF	2008/07/28 12:12
S88	4	"6,862,196"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 14:38
S89	9	("4499452" "4504775" "4713723" "5353001" "5355301" "5359279" "5537021" "6351359" "6511764").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/29 14:38

S90	22	("3900770" "3953816" "3958075" "4021728" "4156148" "4196411" "4215235" "4218724" "4250481" "4257091" "4266140" "4394530" "4425511" "4449165" "4449292" "4488202" "4498120" "4546410" "4546411" "4554613" "4574162" "4577387").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/29 14:44
S91	10	("4713723").URPN.	USPAT	OR	OFF	2008/07/29 14:46
S92	378	(scr triac thyristor) with ("HF" "RF" high near frequency radio near frequency) with gat\$3	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 14:50
S93	378	(scr triac thyristor) with ("HF" "RF" high near frequency or radio near frequency) with gat\$3	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 14:50
S94	354	(scr triac thyristor) with ("HF" "RF" high near frequency or radio near frequency) with (gated gating gate)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 14:50
S95	98	(scr triac thyristor) with ("HF" "RF" high near frequency or radio near frequency) with (gated gating gate) with signal	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 14:51
S96	16	(scr triac thyristor) with ("HF" "RF" high near frequency or radio near frequency) near3 (gated gating gate) near3 signal	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 14:52
S97	8	("3363143" "3702941" "4287465" "4334147" "4344121" "4600877" "4665458").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/29 15:08

S98	2	("4868486").URPN.	USPAT	OR	OFF	2008/07/29 15:11
S99	4	("3140963" "5898205" "6323718").FN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/29 15:12
S100	4	"4,256,982"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 16:09
S101	6	("3423664" "3558983" "3646578" "3681677" "3887836").FN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/07/29 16:11
S102	2	("4256982").URPN.	USPAT	OR	OFF	2008/07/29 16:12
S103	30	"4,149,217"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 16:13
S104	11	"1488306"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 16:19
S105	17	"4,050,006"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 16:20
S106	30	"4,149,217"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 16:22
S107	3	"6,842,118"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/29 16:40

S108	3	"6091087"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:30
S109	5	10/727,189	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:45
S110	21	"3,344,310"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:50
S111	17918	high near frequency with transformer	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:55
S112	120	high near frequency with transformer with printed	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:55
S113	0	high near frequency with transformer with printed with scr	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:56
S114	0	high near frequency with transformer with printed same scr	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:56
S115	0	high near frequency with transformer with printed same (scr triac thyristor)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:56

S116	399	high near frequency with transformer same (scr triac thyristor)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:56
S117	63	high near frequency with transformer same (scr triac thyristor) and gating	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:57
S118	20	high near frequency with transformer same (scr triac thyristor) and pulse near train	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 10:57
S119	15	high near frequency with transformer same printed and driv\$3 with (transistor scr triac thyristor IGBT mosfet fet)	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/30 11:07
S120	425	high near frequency with scr	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 13:57
S121	0	high near frequency with scr with accumulat \$3	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 13:58
S122	4	high near frequency with scr same accumulat\$3	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 13:58
S123	4	scr and pezzani	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 14:02

S124	4	"4,779,036"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 14:06
S125	3	"6,091,087"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/03 20:26
S126	11	"4,630,092"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/04 10:06
S127	4	"4,779,036"	US-PGPUB; USPAT; USOCR; FFRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/11/04 13:33

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